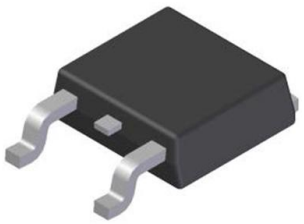
DMTH4004LK3-13 Datasheet



DiGi Electronics Part Number	DMTH4004LK3-13-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMTH4004LK3-13
Description	MOSFET N-CH 40V 100A TO252
Detailed Description	N-Channel 40 V 100A (Tc) 3.9W (Ta), 180W (Tc) Surface Mount TO-252-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMTH4004LK3-13	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
40 V	100A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	3mOhm @ 50A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	83 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	4450 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	3.9W (Ta), 180W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
TO-252-3	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
DMTH4004	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Green

DMTH4004LK3

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

NEW PRODUCT

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C (Note 9)
40V	3mΩ @ V_{GS} = 10V	100A
	5mΩ @ V_{GS} = 4.5V	100A

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

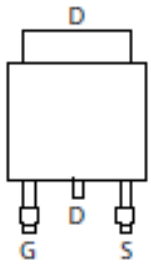
- Rated to 175° C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Rdson – Minimizes Power Losses
- Low Qg – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH4004LK3Q)**

Mechanical Data

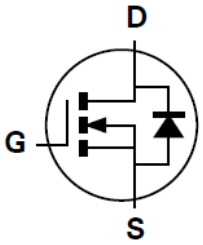
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)

Top View



Pin Out Top View



Equivalent Circuit

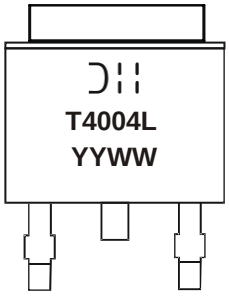
Ordering Information (Notes 4)

Part Number	Case	Packaging
DMTH4004LK3-13	TO252	2,500/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

TO252-3L



=Manufacturer's Marking
T4004L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year
(ex: 15 = 2015)
WW = Week Code (01 to 53)

DIODES INCORPORATED

DMTH4004LK3

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6), V_{GS} = 10V	T_C = +25°C (Note 9) T_C = +100°C	I_D	100 100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	100	A
Avalanche Current, L = 0.2mH		I_{AS}	30	A
Avalanche Energy, L = 0.2mH		E_{AS}	90	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.9	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	38	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	180	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current, T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.4	3	mΩ	V_{GS} = 10V, I_D = 50A
		—	4	5	mΩ	V_{GS} = 4.5V, I_D = 50A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 50A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	4,450	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	1,407	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	74	—	pF	
Gate Resistance	R_g	—	0.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	35	—	nC	V_{DS} = 20V, I_D = 30A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	83	—	nC	
Gate-Source Charge	Q_{gs}	—	10	—	nC	
Gate-Drain Charge	Q_{gd}	—	11.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.9	—	ns	V_{GS} = 10V, V_{DS} = 20V, R_g = 1.6Ω, I_D = 30A
Turn-On Rise Time	t_r	—	13.2	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	25.8	—	ns	
Turn-Off Fall Time	t_F	—	7.9	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	48	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	72	—	nC	I_F = 50A, di/dt = 100A/µs

Notes: 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
6. Thermal resistance from junction to solder point (on the exposed drain pin).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.
9. Package Limited.

NEW PRODUCT

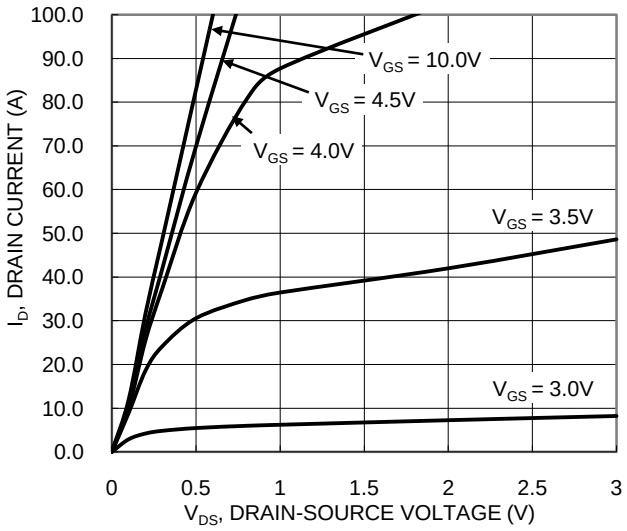


Figure 1. Typical Output Characteristic

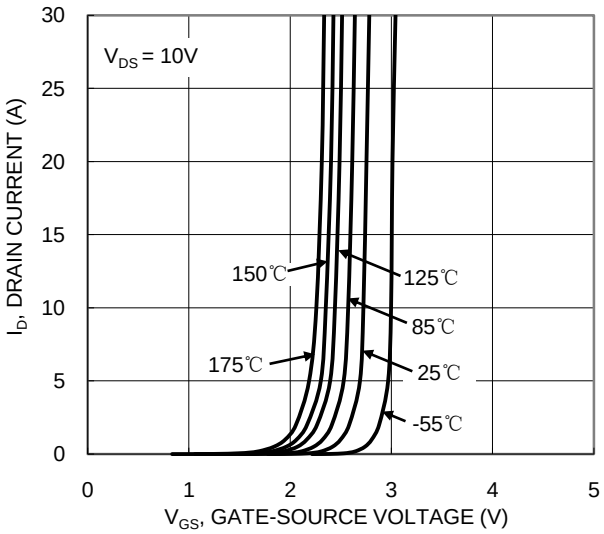


Figure 2. Typical Transfer Characteristic

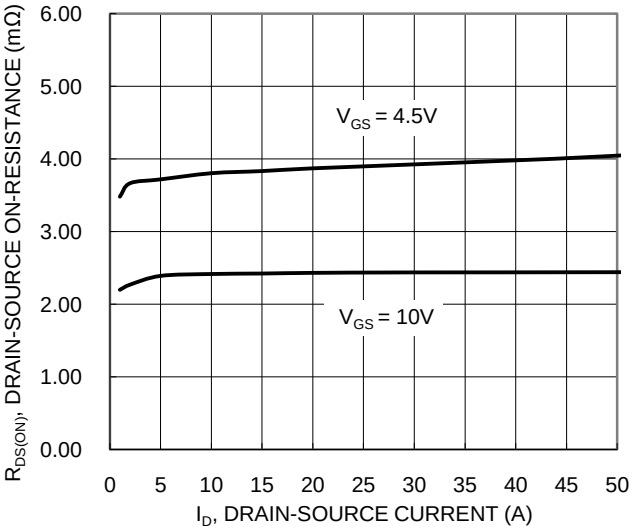


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

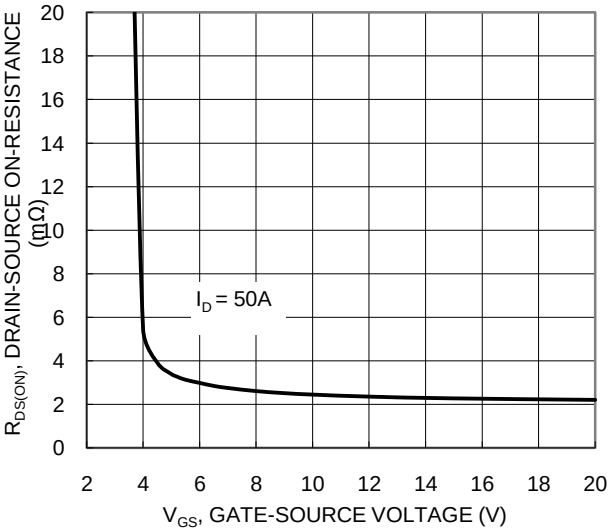


Figure 4. Typical Transfer Characteristic

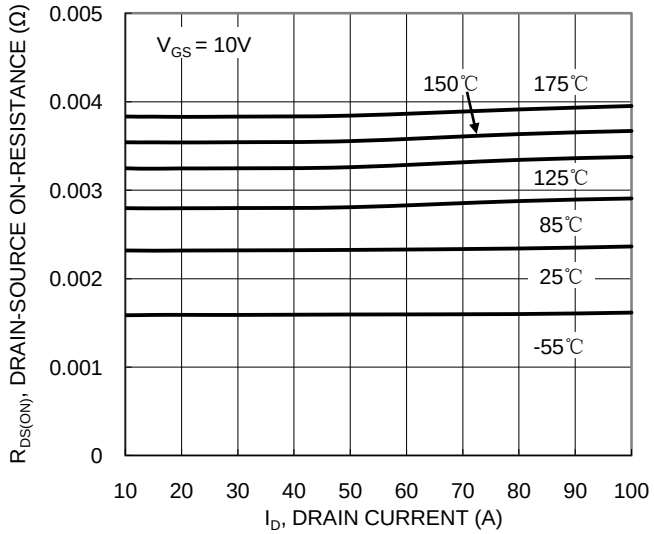


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

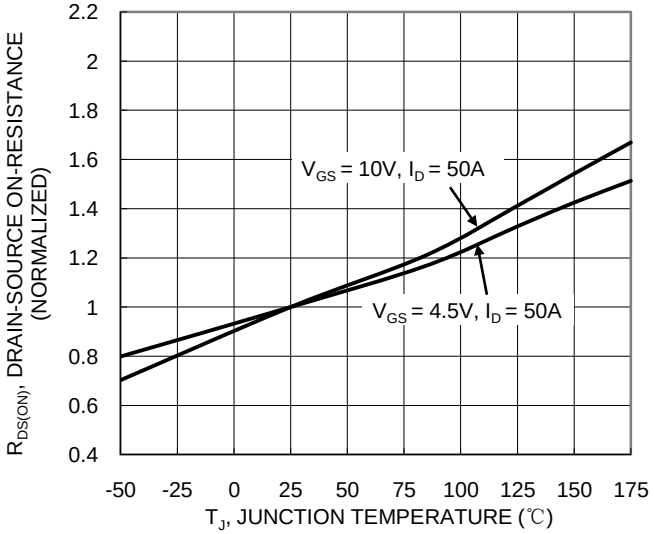


Figure 6. On-Resistance Variation with Temperature

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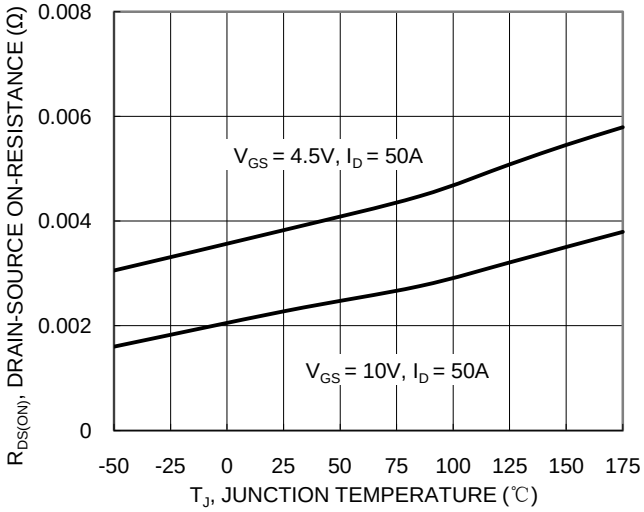

Figure 7. On-Resistance Variation with Temperature

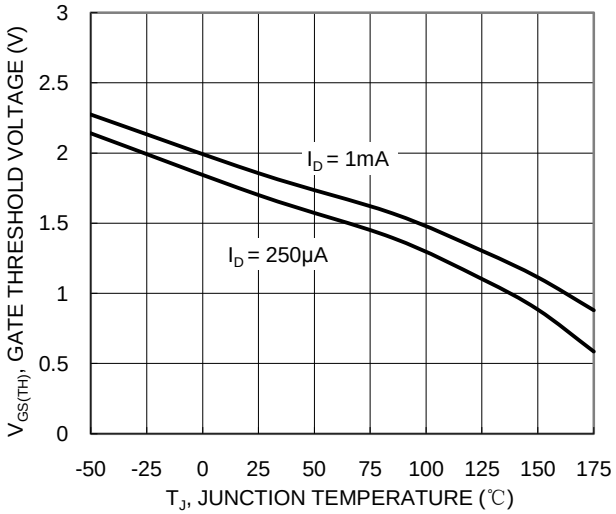

Figure 8. Gate Threshold Variation vs. Temperature

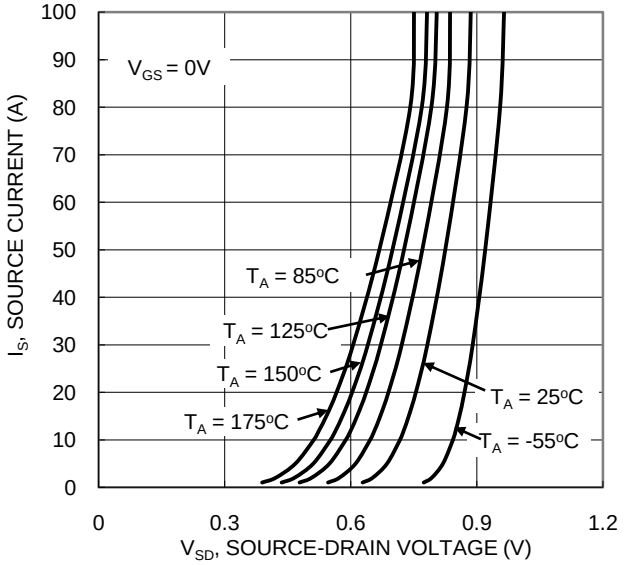

Figure 9. Diode Forward Voltage vs. Current

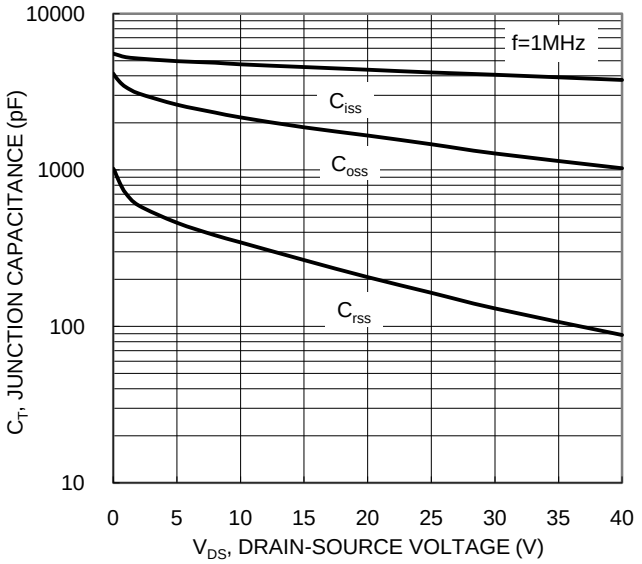

Figure 10. Typical Junction Capacitance

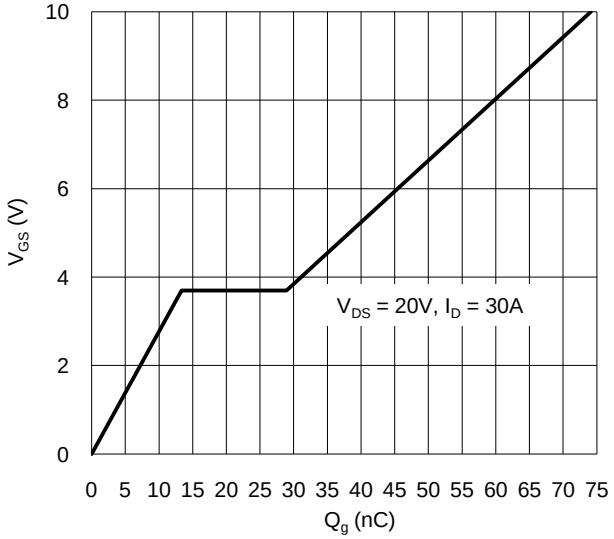

Figure 11. Gate Charge

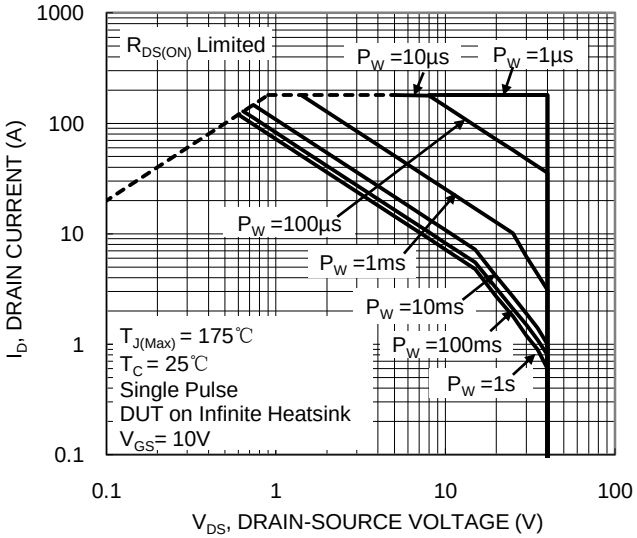

Figure 12. SOA, Safe Operation Area

NEW PRODUCT

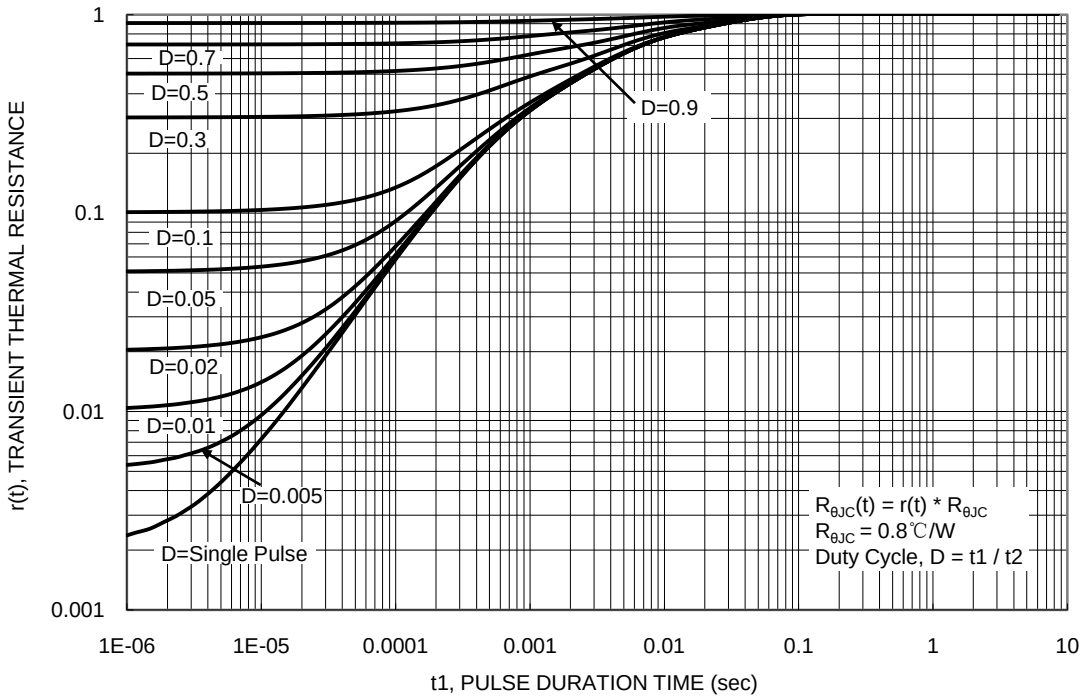

Figure 13. Transient Thermal Resistance

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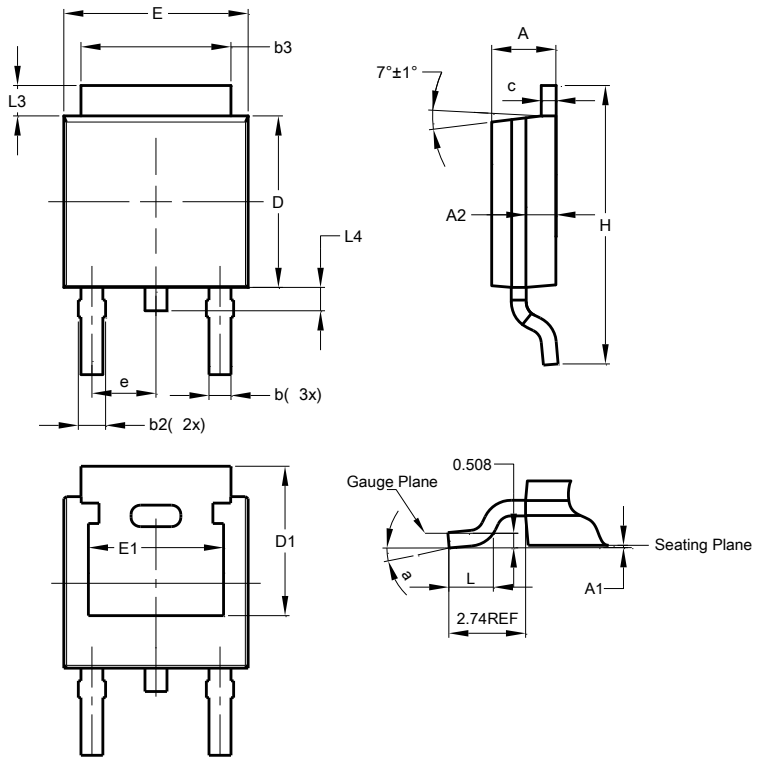
Package Outline

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO252 (DPAK)

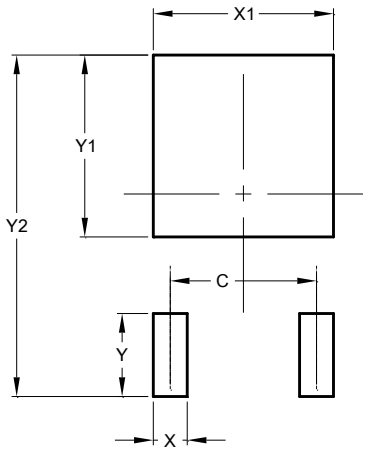


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

NEW PRODUCT

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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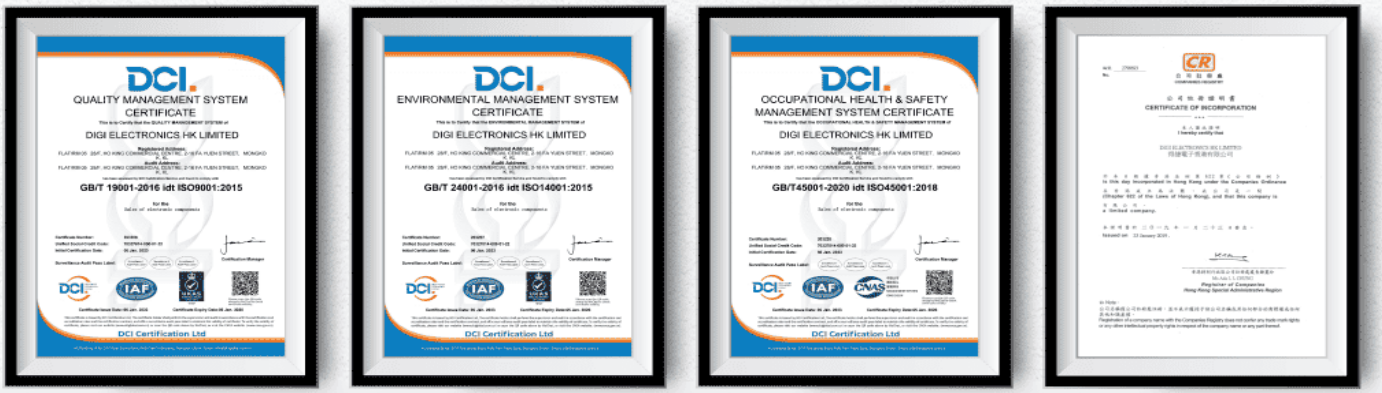

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